

METHOD FOR PRODUCING MULTILAYER BODY, AND RESIN COMPOSITION

ABSTRACT

The present invention addresses the problem of conventional insulating layers that are formed of SiO_2 , the problem being low bonding strength. The present invention also addresses the problem of conduction failure of an electrode or reliability decrease of an obtained multilayer body in cases where a semiconductor element is bonded by means of C2W. The present invention provides a method for producing a multilayer body, the method comprising: a step (I) of preparing a first substrate which is provided, on the same surface of a substrate main body, with an exposed metal electrode (A-1) and an exposed resin layer (B-1); a step (II) of preparing a second substrate which is provided, on the same surface of a substrate main body, with an exposed metal electrode (A-2) and an exposed resin layer (B-2), or alternatively with an exposed metal electrode (A-2) and an exposed inorganic insulating layer (C); and a step (III) of bonding the first substrate and the second substrate to each other by means of direct bonding, while having at least a part of the metal electrode (A-1) and the metal electrode (A-2) face each other and having at least a part of the resin layer (B-1)

and the resin layer (B-2) face each other, or alternatively having at least a part of the metal electrode (A-1) and the metal electrode (A-2) face each other and having at least a part of the resin layer (B-1) and the inorganic insulating layer (C) face each other. With respect to this method for producing a multilayer body, the resin layer (B-1) and the resin layer (B-2) each contain a specific resin.

[FIG. 2]